

Low Distortion Internally Matched Power GaAs FETs (C-Band)

Features

- Low intermodulation distortion
 - $IM_3 = -45$ dBc at $P_o = 34.5$ dBm,
 - Single carrier level
- High power
 - $P_{1dB} = 45$ dBm at 5.0 GHz to 5.3 GHz
- High gain
 - $G_{1dB} = 9$ dB at 5.0 GHz to 5.3 GHz
- Broad band internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 5.0 \sim 5.3$ GHz	dBm	44.0	45.0	–
Power Gain at 1dB Compression Point	G_{1dB}		dB	8.0	9.0	–
Drain Current	I_{DS1}		A	–	8.0	9.0
Gain Flatness	ΔG		dB	–	–	± 0.8
Power Added Efficiency	η_{add}		%	–	35	–
3rd Order Intermodulation Distortion	IM_3	Note 1	dBc	-42	-45	–
Drain Current	I_{DS2}		A	–	8.0	9.0
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th}(c-c)$	$^\circ\text{C}$	–	–	80

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 10.5A$	mS	–	6300	–
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 140mA$	V	-2.0	-3.5	-5.0
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	20	26
Gate-Source Breakdown Voltage	V_{GSO}	$I_{GS} = -420\mu A$	V	-5	–	–
Thermal Resistance	$R_{th}(c-c)$	Channel to case	$^\circ\text{C}/W$	–	0.8	1.0

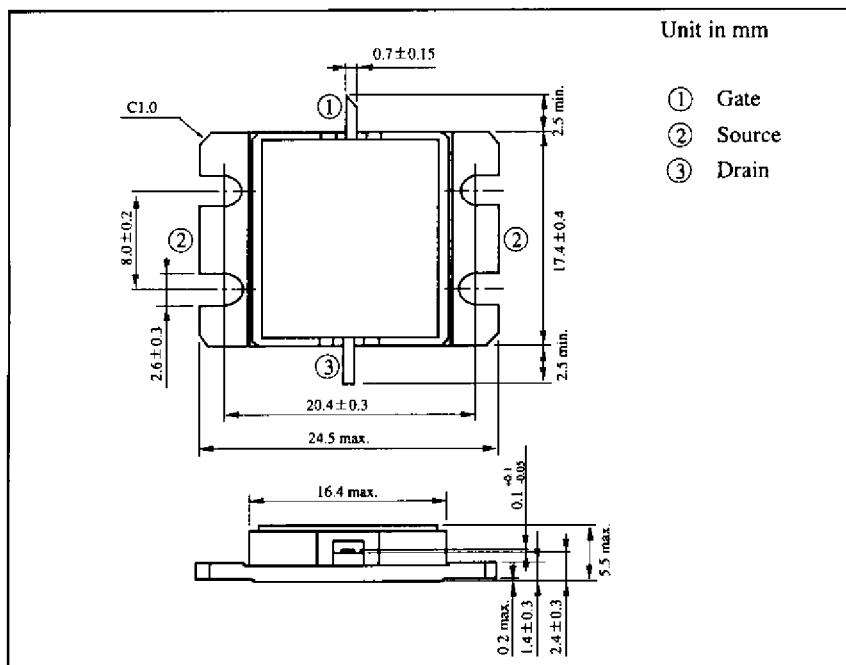
Note 1: 2 tone Test Pout = 34.5dBm Single Carrier Level.

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Absolute Maximum Ratings (Ta = 25° C)

Characteristic	Symbol	Unit	Rating
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	26
Total Power Dissipation (T _c = 25°C)	P _T	W	120
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

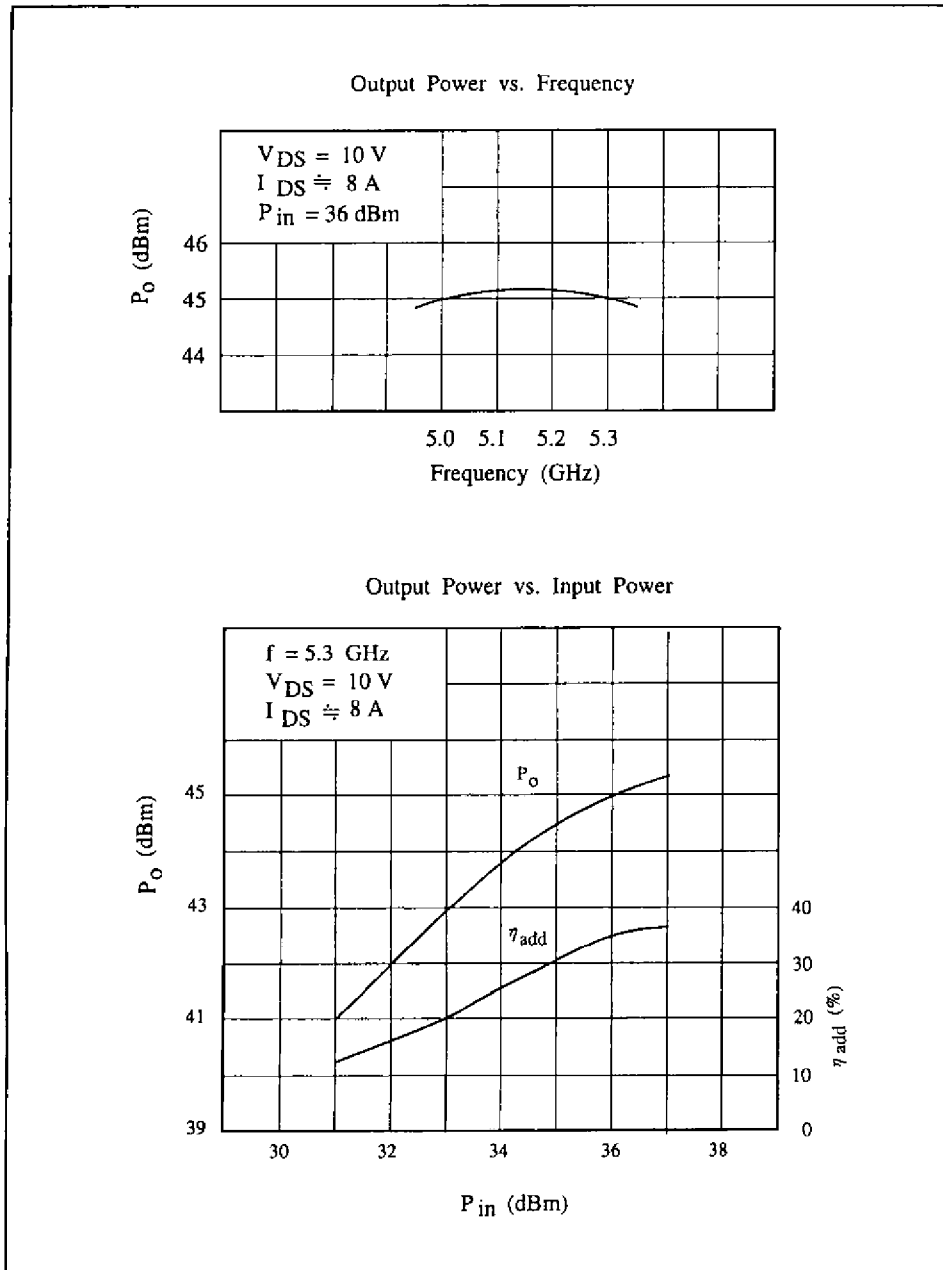
Package Outline (2-16G1B)



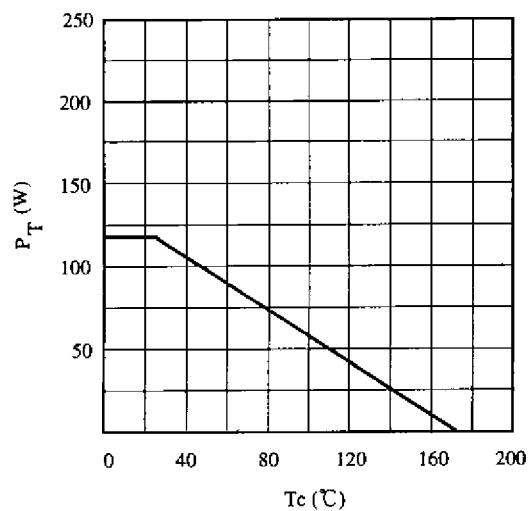
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF Performances



Power Dissipation vs. Case Temperature



IM_3 vs. Output Power Characteristics

